

< C band internally matched power GaAs FET >

MGFC42V5964

5.9 - 6.4 GHz BAND / 16W

DESCRIPTION

The MGFC42V5964 is an internally impedance-matched GaAs power FET especially designed for use in 5.9 - 6.4 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation

Internally matched to 50(ohm) system High output power

- P1dB=16W (TYP.) @f=5.9 6.4GHz • High power gain
- GLP=9dB (TYP.) @f=5.9 6.4GHz High power added efficiency
- P.A.E.=31% (TYP.) @f=5.9 6.4GHz
- Low distortion [item -51] IM3=-45dBc (TYP.) @Po=32dBm S.C.L

APPLICATION

- item 01 : 5.9 6.4 GHz band power amplifier
- item 51 : 5.9 6.4 GHz band digital radio communication

QUALITY

• IG

RECOMMENDED BIAS CONDITIONS

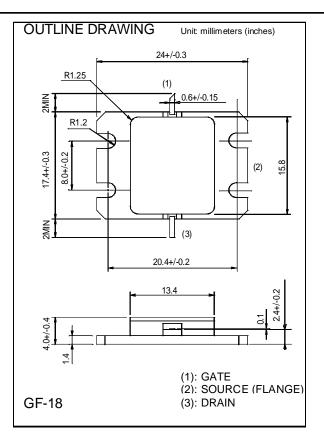
VDS=10V
ID=4.5A Refer to Bias Procedure
RG=50ohm

Absolute maximum ratings (Ta=25°C)

Symbol	Parameter	Ratings	Unit					
VGDO	Gate to drain breakdown voltage	-15	V					
VGSO	Gate to source breakdown voltage	-15	V					
ID	Drain current	15	А					
IGR	Reverse gate current	-40	mA					
IGF	Forward gate current	84	mA					
PT *1	Total power dissipation	78.9	W					
Tch	Cannel temperature	175	°C					
Tstg	Storage temperature	-65 to +175	°C					

*1 : Tc=25°C

Electrical characteristics (Ta=25°C)



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Symbol	Parameter	Test conditions	Limits		Unit	
			Min.	Тур.	Max.	
IDSS	Saturated drain current	VDS=3V,VGS=0V	-	9	12	А
gm	Transconductance	VDS=3V,ID=4.4A	-	4	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=80mA	-2	-3	-4	V
P1dB	Output power at 1dB gain compression	VDS=10V,ID(RF off)=4.5A	41.5	42.5	-	dBm
GLP	Linear Power Gain	f=5.9 – 6.4GHz	8	9	-	dB
ID	Drain current		-	4.5	-	А
P.A.E.	Power added efficiency		-	31	-	%
IM3 *2	3rd order IM distortion		-42	-45	-	dBc
Rth(ch-c) *3	Thermal resistance	delta Vf method	-	1.6	1.9	°C/W

*2 :item -51 ,2 tone test,Po=32dBm Single Carrier Level ,f=6.4GHz,delta f=10MHz

*3 :Channel-case

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